优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(on)}$ Max	I_D T_A = +25°C
-40V	60mΩ @ V_{GS} = -10V	-6.4A
	100mΩ @ V_{GS} = -4.5V	-5.0A

Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed

Description and Applications

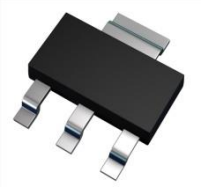
This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- DC-DC converters
- Power management functions
- Backlighting

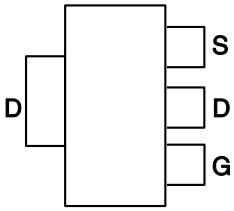
Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.112 grams (Approximate)

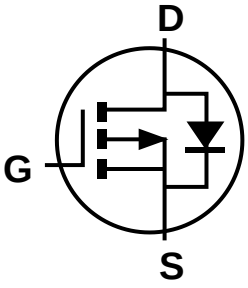
SOT223 (Type DN)



Top View



Pin Out - Top View



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-40	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current, V_{GS} = -10V	Steady State	T_A = +25°C (Note 5) T_A = +70°C (Note 5) T_A = +25°C (Note 6)	I_D	-6.4 -5.1 -4.6	A
Maximum Body Diode Forward Current (Note 5)			I_S	-6.4	A
Pulsed Drain Current (Note 7)			I_{DM}	-21	A
Pulsed Source Current (Note 7)			I_{SM}	-21	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

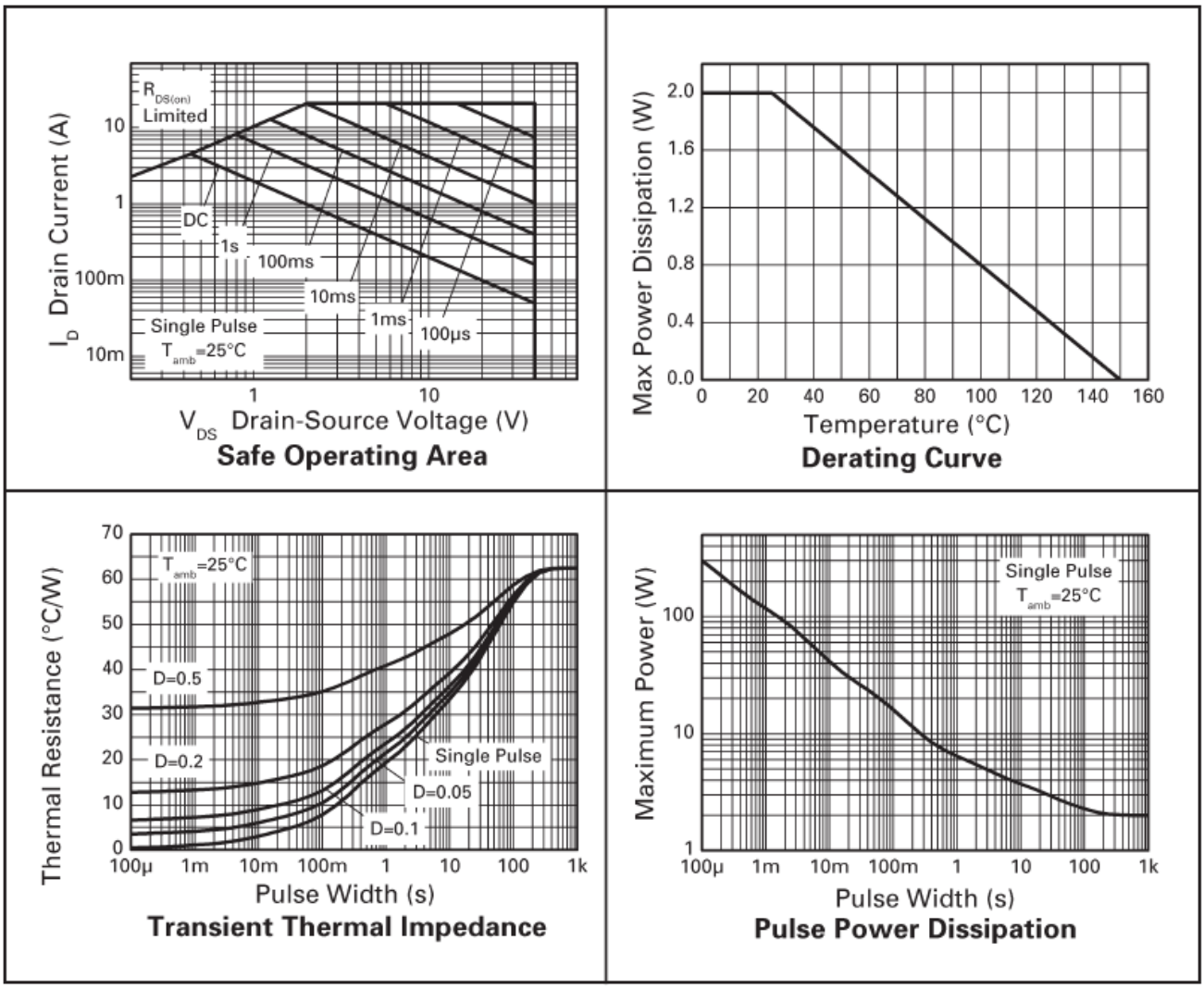
Characteristic		Symbol	Value	Units
Total Power Dissipation Linear Derating Factor	T_A = +25°C (Note 6)	P_D	2.0 16	W mW/°C
Total Power Dissipation Linear Derating Factor	T_A = +25°C (Note 5)	P_D	3.9 31	W mW/°C
Thermal Resistance, Junction to Ambient	Steady State (Note 6)	$R_{\theta JA}$	62.5	°C/W
	Steady State (Note 5)		32	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

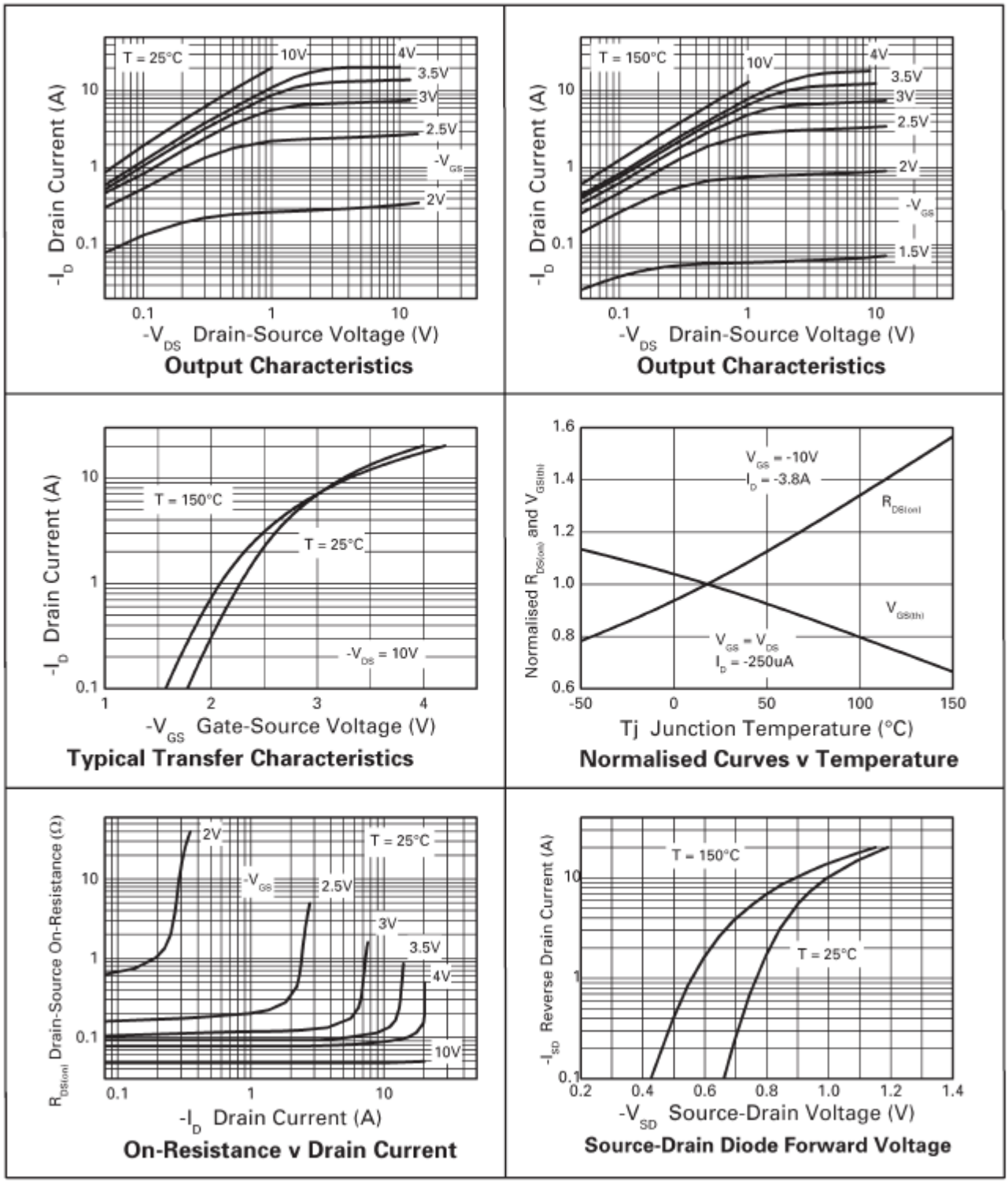
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-40	—	—	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1.0	μA	V_{DS} = -40V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	—	—	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance (Note 9)	$R_{DS(on)}$	—	—	60	mΩ	V_{GS} = -10V, I_D = -3.8A
		—	—	100		V_{GS} = -4.5V, I_D = -2.9A
Diode Forward Voltage (Note 9)	V_{SD}	—	-0.85	-1.2	V	V_{GS} = 0V, I_S = -3.4A
Forward Transconductance (Notes 9 & 10)	g_{fs}	—	8.85	—	S	V_{DS} = -15V, I_D = -3.8A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	1,007	—	pF	V_{DS} = -20V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	130	—		
Reverse Transfer Capacitance	C_{rss}	—	85	—		
Total Gate Charge (V_{GS} = -5.0V)	Q_g	—	13.6	—	nC	V_{DS} = -20V, I_D = -3.8A
Total Gate Charge (V_{GS} = -10V)	Q_g	—	26.1	—		
Gate-Source Charge	Q_{gs}	—	2.8	—		
Gate-Drain Charge	Q_{gd}	—	4.8	—		
Turn-On Delay Time	$t_{D(on)}$	—	2.33	—	ns	V_{GS} = -10V, V_{DD} = -20V, R_G = 6.0Ω I_D = -1.0A
Turn-On Rise Time	t_r	—	8.84	—		
Turn-Off Delay Time	$t_{D(off)}$	—	29.18	—		
Turn-Off Fall Time	t_f	—	12.54	—		
Body Diode Reverse Recovery Time	t_{rr}	—	27.2	—	ns	I_F = -3A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q_{rr}	—	25.4	—	nC	

Notes:
5. For a device surface mounted on FR4 PCB measured at t ≤ 10s.
6. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
7. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width limited by maximum junction temperature.
8. Short duration pulse test used to minimize self-heating effect.
9. Measured under pulsed conditions. Width ≤ 300μs. Duty cycle ≤ 2%.
10. Guaranteed by design. Not subject to product testing.

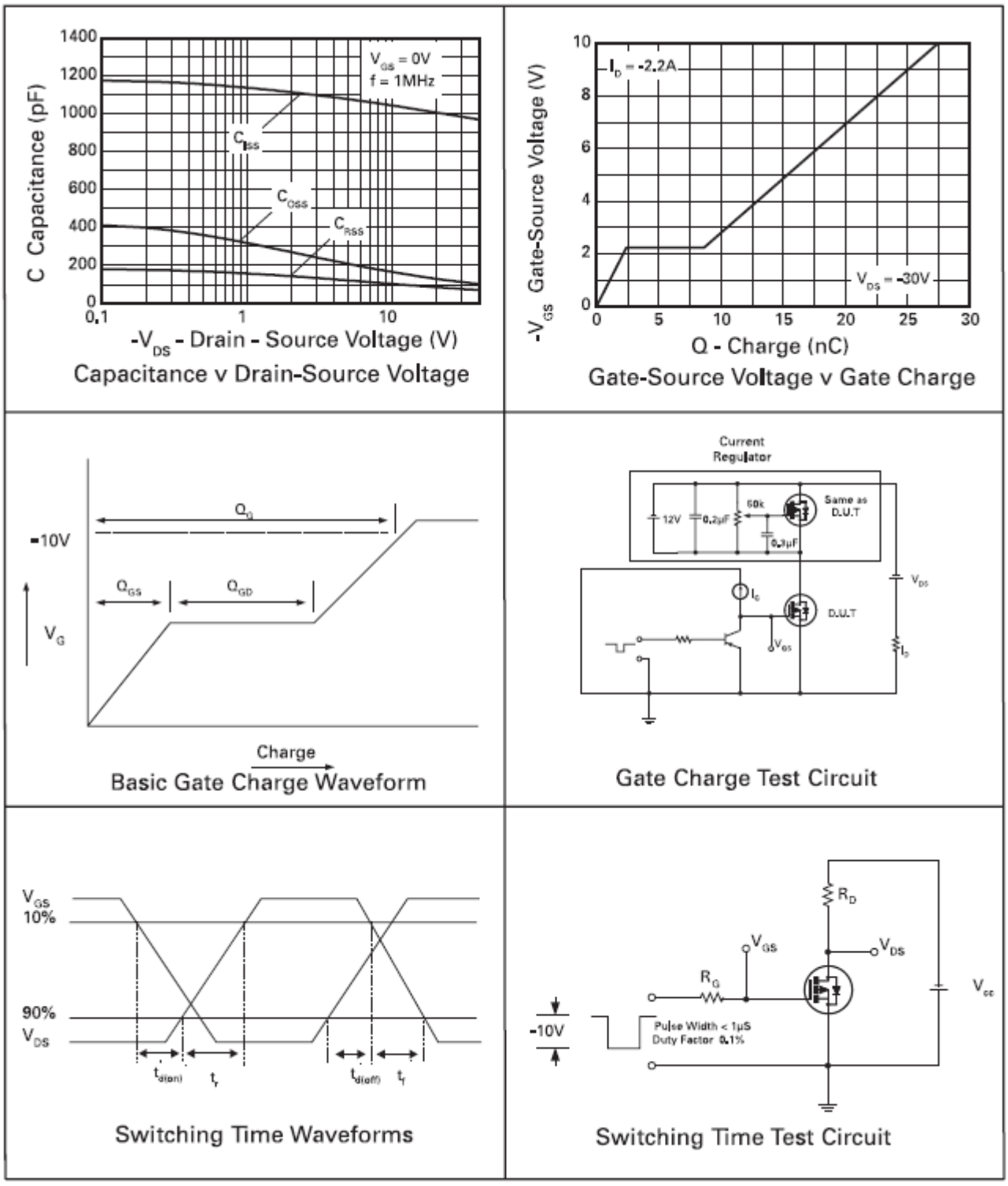
Typical Characteristics



Typical Characteristics (continued)

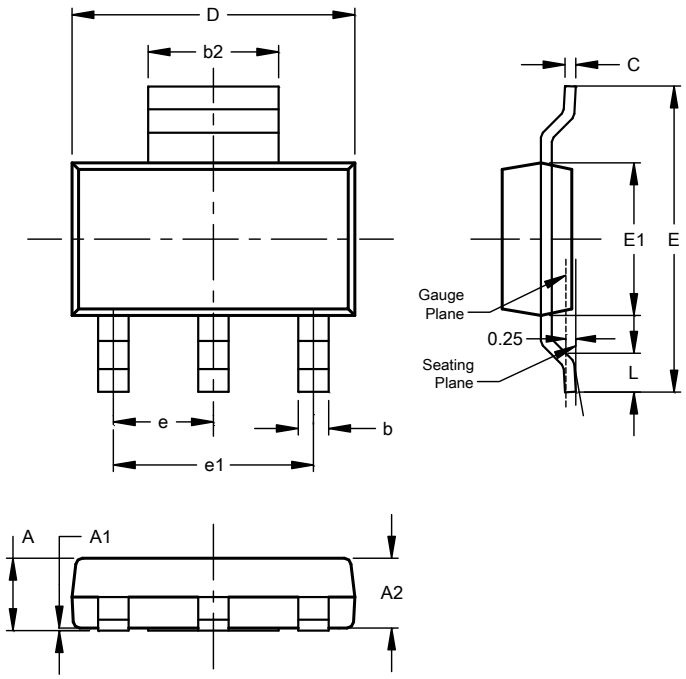


Typical Characteristics (continued)



Package Outline Dimensions

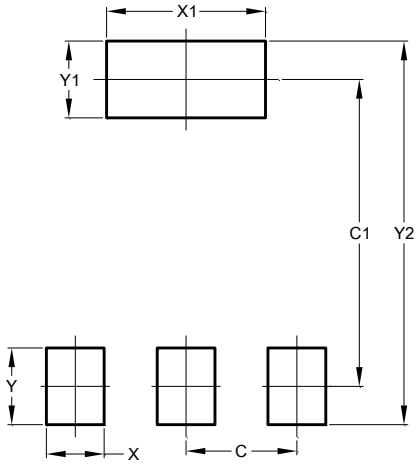
SOT223 (Type DN)



SOT223 (Type DN)			
Dim	**Min**	**Max**	**Typ**
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

Suggested Pad Layout

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00